SQJ410EP



Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	30				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0039				
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0042				
I _D (A)	32				
Configuration	Single				

PowerPAK® SO-8L Single

FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_a and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ410EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted	l)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C		32		
	T _C = 125 °C	I _D	32		
Continuous Source Current (Diode Conduction) ^a		I _S	32	А	
Pulsed Drain Current ^b		I _{DM}	128		
Single Pulse Avalanche Current		I _{AS}	58		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	168	mJ	
Mauinum Davier Diasia atia at	T _C = 25 °C	5	83	14/	
Maximum Power Dissipation ^b	T _C = 125 °C	PD	27	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	*0	
Soldering Recommendations (Peak Temperature) ^{e, f}			260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	65	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.8	0/10	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 $\mu s,\,duty\,cycle \leq$ 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See Solder Profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

S12-1860-Rev. C, 13-Aug-12

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	30	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		1.5	2.0	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α	
		$V_{GS} = 10 V$	I _D = 10.3 A	-	0.0037	0.0039	μΑ Α Α Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο Ο	1
Durin Course On Otata Desistence?		V _{GS} = 10 V	I _D = 10.3 A, T _J = 125 °C	-	0.0045	0.0060	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 10.3 A, T _J = 175 °C	-	0.0055	0.0070	Ω	
		$V_{GS} = 4.5 V$	I _D = 8.7 A	-	0.0035	0.0042		
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 16 A	-	93	-	S	
Dynamic ^b	•	• •						
Input Capacitance	C _{iss}			-	4965	6210		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 15 V, f = 1 MHz	-	806	1010	pF	
Reverse Transfer Capacitance	C _{rss}			-	325	410		
Total Gate Charge ^c	Qg			-	73.5	110		
Gate-Source Charge ^c	Q _{gs}	$\begin{array}{c c} & V_{GS} \\ \hline & V_{DS} = \\ & V_{DS} = \\ \hline & V_{GS} = 0 \ V \\ \hline & V_{GS} = 0 \ V \\ \hline & V_{GS} = 0 \ V \\ \hline & V_{GS} = 10 \ V \\ \hline & V_{DS} = 10 \ V \\$	V _{DS} = 15 V, I _D = 15 A	-	12.8	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	8.2	-		
Gate Resistance	R _g		f = 1 MHz	0.6	1.0	1.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	15	23		
Rise Time ^c	t _r	- V_p =	= 15 V, R _I = 1.5 Ω	-	11	17		
Turn-Off Delay Time ^c	t _{d(off)}		$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	40	60	ns	
Fall Time ^c	t _f	1		-	9	14	1	
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	128	Α	
Forward Voltage	V _{SD}	I _F :	= 10 A, V _{GS} = 0	-	0.75	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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- 55 °C

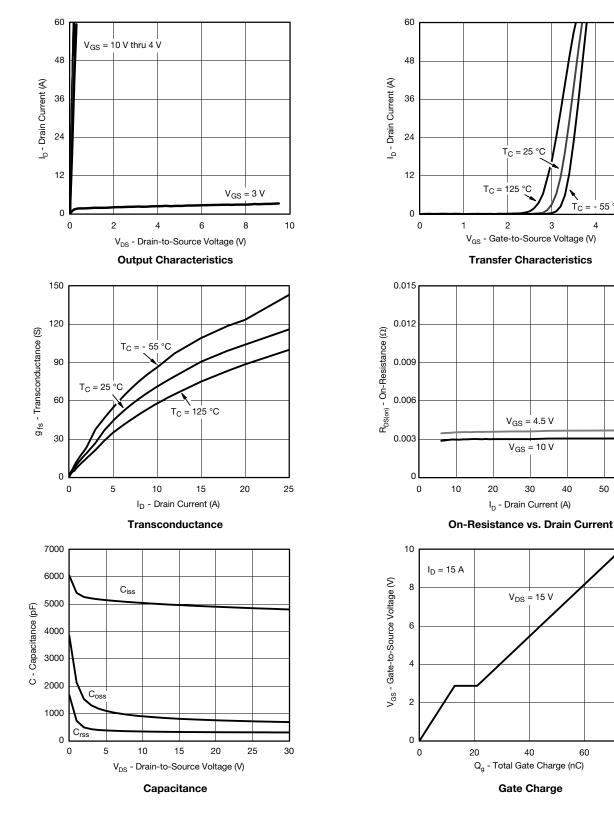
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

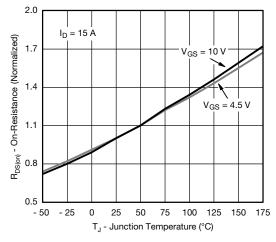


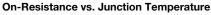
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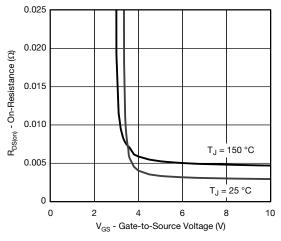
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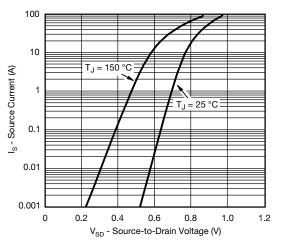
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



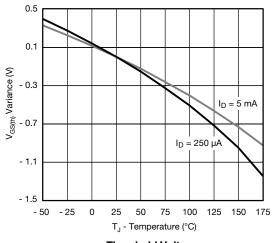




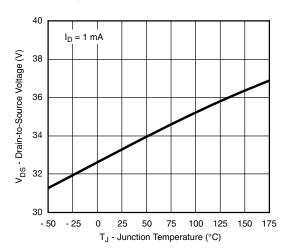
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



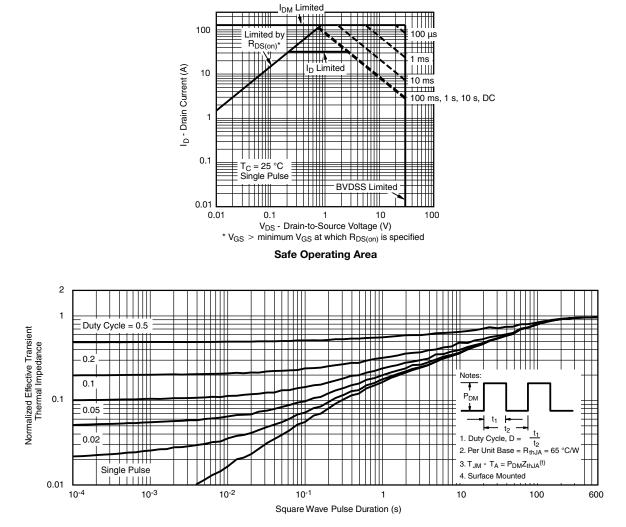
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

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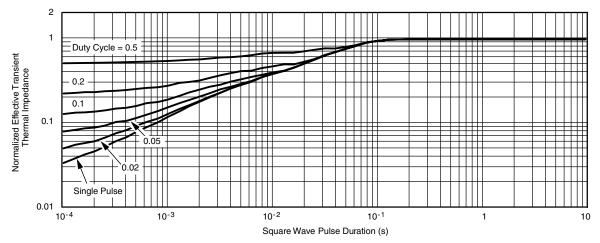
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67003.

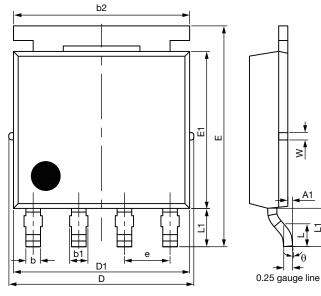


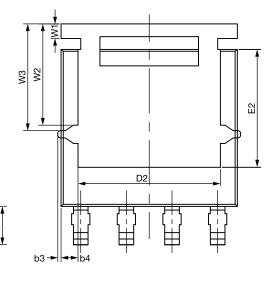


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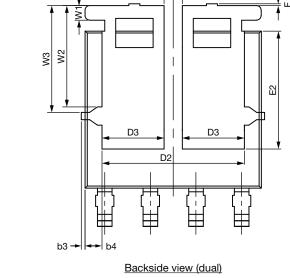
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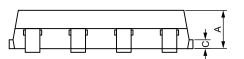




Topside view

Backside view (single)





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Package Information



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DIM	MILLIMETERS			INCHES				
DIM.	MIN.	NOM.	MAX.	MIN.	MAX.			
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	3.18	3.28	3.38	0.125	0.129	0.133		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23			0.009			
W1	0.41			0.016				
W2	2.82			0.111				
W3	2.96		0.117					
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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